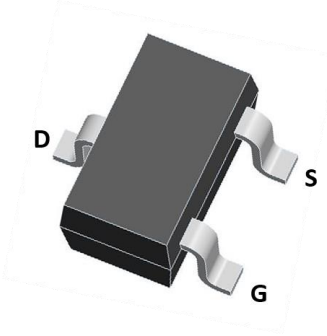
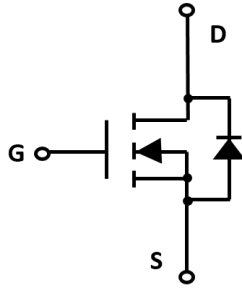
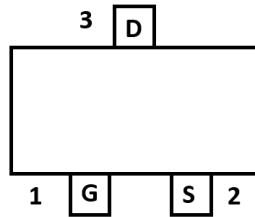


N-Channel Enhancement Mode Field Effect Transistor



SOT-323



Product Summary

- V_{DS} 100V
- I_D 200mA
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <5.0ohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) <5.5ohm

General Description

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- High density cell design for low $R_{DS(ON)}$
- Fast Switching Speed

Applications

- Small servo motor control
- Power MOSFET gate drivers
- Switching application

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	100	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current	I_D	$T_A=25^\circ C$ @ Steady State	200
		$T_A=70^\circ C$ @ Steady State	160
Pulsed Drain Current ^A	I_{DM}	800	mA
Total Power Dissipation @ $T_A=25^\circ C$	P_D	350	mW
Thermal Resistance Junction-to-Ambient @ Steady State ^B	$R_{\theta JA}$	357	$^\circ C/W$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
BSS123	F2	B123.	3000	30000	120000	7" reel



BSS123W

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS1}	V _{GS} = ±20V, V _{DS} =0V			±100	nA
	I _{GSS2}	V _{GS} = ±10V, V _{DS} =0V			±50	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	1	1.8	3.0	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D =200mA		3.0	5.0	Ω
		V _{GS} = 4.5V, I _D =200mA		3.5	5.5	
Diode Forward Voltage	V _{SD}	I _S =200mA, V _{GS} =0V			1.2	V
Maximum Body-Diode Continuous Current	I _S				200	mA
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHZ		14		pF
Output Capacitance	C _{oss}			10		
Reverse Transfer Capacitance	C _{rss}			5		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =50V, I _D =0.2A		1.8	2.5	nC
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =50V, I _D =0.2A, R _{GEN} =6Ω		1.7		ns
Turn-on Rise Time	t _r			9		
Turn-off Delay Time	t _{D(off)}			17		
Turn-off fall Time	t _f			7		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.



■ Typical Performance Characteristics

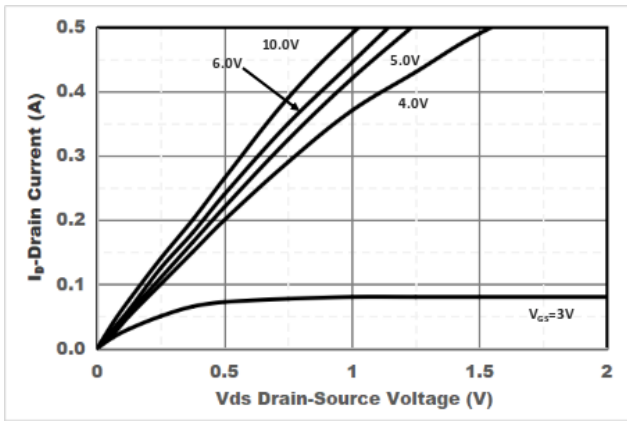


Figure1. Output Characteristics

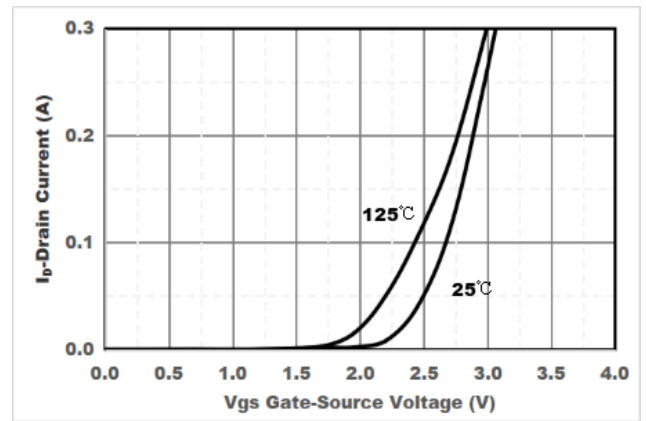


Figure2. Transfer Characteristics

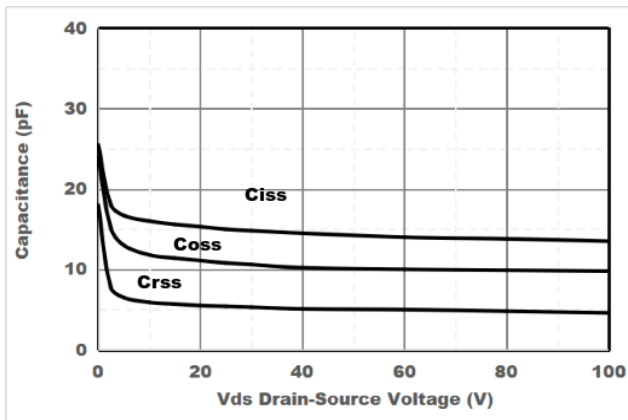


Figure3. Capacitance Characteristics

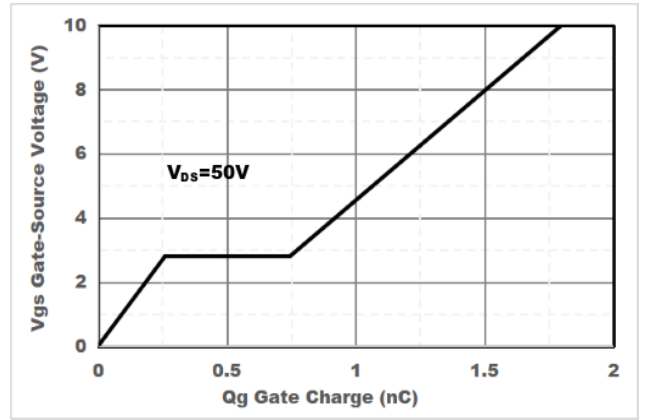


Figure4. Gate Charge

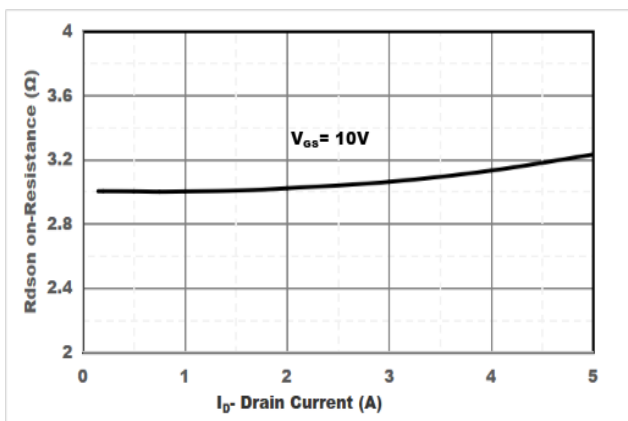


Figure5. Drain-Source on Resistance

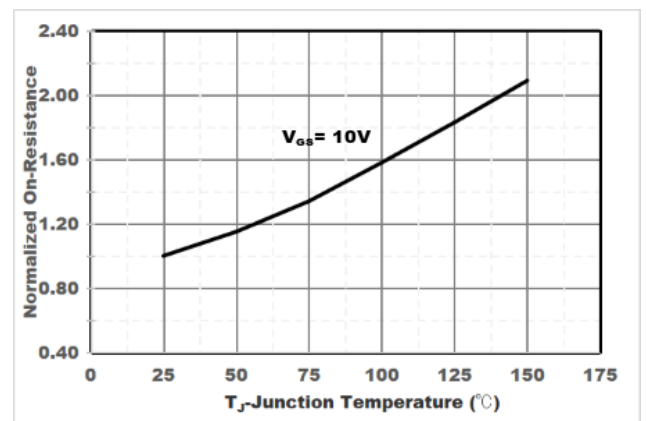


Figure6. Drain-Source on Resistance

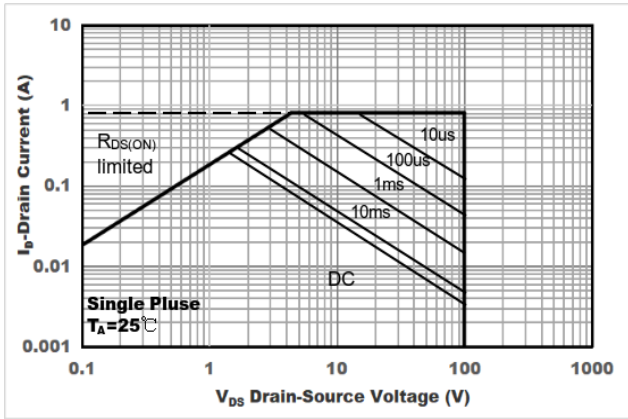


Figure7. Safe Operation Area

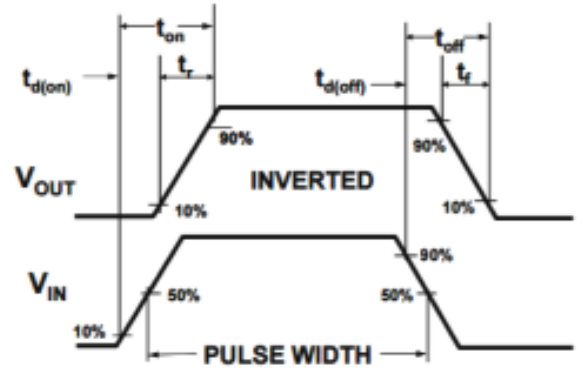
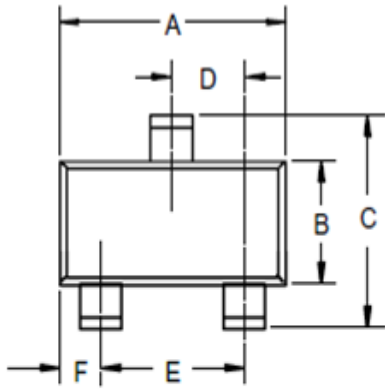
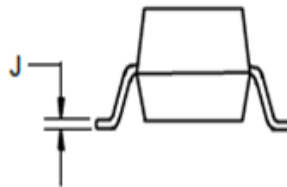
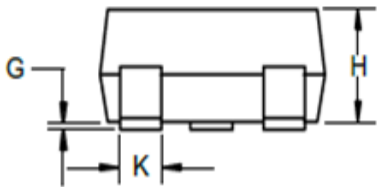


Figure8. Switching wave

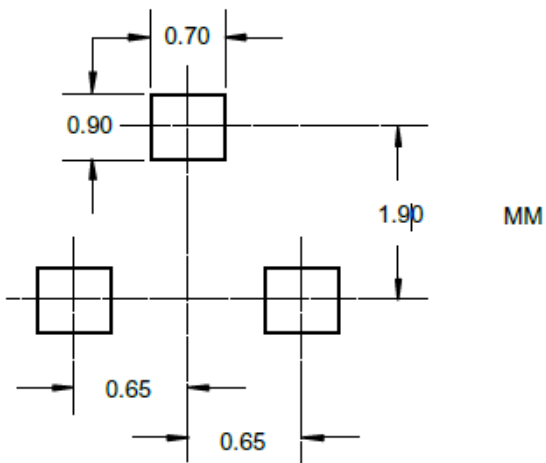
■ SOT-323 Package information



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.071	.087	1.80	2.20	
B	.045	.053	1.15	1.35	
C	.083	.096	2.10	2.45	
D	.026 Nominal		0.65Nominal		
E	.047	.055	1.20	1.40	
F	.012	.016	.30	.40	
G	.000	.004	.000	.100	
H	.035	.039	.90	1.00	
J	.004	.010	.100	.250	
K	.006	.016	.15	.40	



■ SOT-323 Suggested Pad Layout





BSS123W

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